

MOS Field Effect Transistor

2SK1483

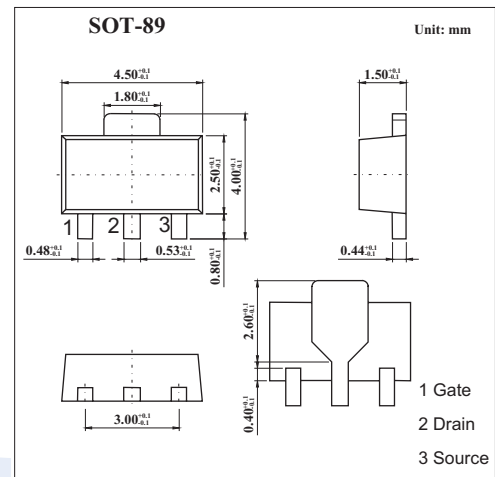
■ Features

- Can be driven directly an IC operating with a 5V single power supply.

- Low ON-state resistance

$R_{DS(on)}=0.8\ \Omega$ MAX. At $V_{GS}=4V, I_D=0.5A$

$R_{DS(on)}=0.4\ \Omega$ MAX. At $V_{GS}=10V, I_D=0.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	30	V
Gate to source voltage	V_{GS}	± 20	V
Drain current (DC)	I_D	± 2.0	A
Drain current(pulse) *	I_D	± 4.0	A
Power dissipation	P_D	2.0	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\text{ms}$, duty cycle $\leq 5\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=30V, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0$			± 5.0	μA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1\text{mA}$	0.9	1.2	1.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=0.5A$	20	38		ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.0V, I_D=0.5A$		22	40	Ω
		$V_{GS}=10V, I_D=0.5A$		14	20	Ω
Input capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1\text{MHz}$		8		pF
Output capacitance	C_{oss}			7		pF
Reverse transfer capacitance	C_{rss}			3		pF
Turn-on delay time	$t_{d(on)}$	$I_D=0.5A, V_{GS(on)}=10V, R_L=50\ \Omega, V_{DD}=25V, R_G=10\ \Omega$		15		ns
Rise time	t_r			50		ns
Turn-off delay time	$t_{d(off)}$			420		ns
Fall time	t_f			240		ns

■ Marking

Marking	NB
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